# **High Speed Dual MOSFET Driver**

#### **Features**

- ▶ 6ns rise and fall time with 1000pF load
- ▶ 2.0A peak output source/sink current
- ▶ 1.2V to 5V input CMOS compatible
- 4.5V to 13V total supply voltage
- Smart logic threshold
- Low jitter design
- Two matched channels
- Outputs can swing below ground
- Low inductance package
- ► Thermally-enhanced package

### **Applications**

- Medical ultrasound imaging
- ▶ Piezoelectric transducer drivers
- Nondestructive evaluation
- ► PIN diode driver
- CCD Clock driver/buffer
- High speed level translator

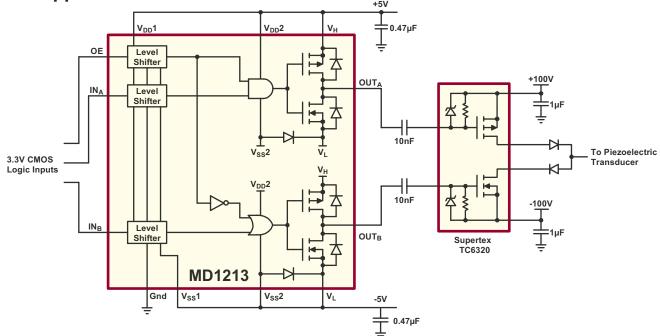
#### **General Description**

The Supertex MD1213 is a high speed, dual MOSFET driver. It is designed to drive high voltage P and N-channel MOSFET transistors for medical ultrasound and other applications requiring a high output current for a capacitive load. The high-speed input stage of the MD1213 can operate from 1.2V to 5.0V logic interface with an optimum operating input signal range of 1.8V to 3.3V. An adaptive threshold circuit is used to set the level translator switch threshold to the average of the input logic 0 and logic 1 levels. The input logic levels may be ground referenced, even though the driver is putting out bipolar signals. The level translator uses a proprietary circuit, which provides DC coupling together with high-speed operation.

The output stage of the MD1213 has separate power connections enabling the output signal L and H levels to be chosen independently from the supply voltages used for the majority of the circuit. As an example, the input logic levels may be 0 and 1.8volts, the control logic may be powered by +5.0V and -5.0V, and the output L and H levels may be varied anywhere over the range of -5.0V to +5.0V. The output stage is capable of peak currents of up to ±2.0A, depending on the supply voltages used and load capacitance present.

The OE pin serves a dual purpose. First, its logic H level is used to compute the threshold voltage level for the channel input level translators. Secondly, when OE is low, the outputs are disabled, with the A output high and the B output low. This assists in properly precharging the AC coupling capacitors that may be used in series in the gate drive circuit of an external PMOS and NMOS transistor pair.

## **Typical Application Circuit**



#### **Ordering Information**

DEVICE	Package Option
DEVICE	12-Lead 4x4x0.8pitch QFN
MD1213	MD1213K6-G

-G indicates package is RoHS compliant ('Green')





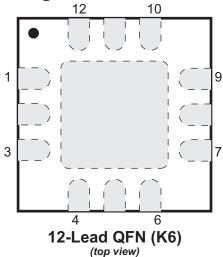


## **Absolute Maximum Ratings**

Parameter	Value
V <sub>DD</sub> -V <sub>SS</sub> , logic supply voltage	-0.5V to +13.5V
V <sub>H</sub> , output high supply voltage	$V_L$ - 0.5V to $V_{DD}$ +0.5V
V <sub>L</sub> , output low supply voltage	$V_{SS}$ - 0.5V to $V_H$ +0.5V
V <sub>ss</sub> , low side supply voltage	-7.0V to +0.5V
Logic input levels	$V_{ss}$ -0.5V to $V_{ss}$ +7.0V
Maximum junction temperature	+125°C
Storage temperature	-65°C to 150°C
Operating temperature	-20°C to 85°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

### **Pin Configuration**



## **Package Marking**



Y = Last Digit of Year Sealed W = Code for Week Sealed L = Lot Number

\_\_\_ = "Green" Packaging

12-Lead QFN (K6)

#### **DC Electrical Characteristics**

(Over operating conditions unless otherwise specified,  $V_H = V_{DD1} = V_{DD2} = 12V$ ,  $V_I = V_{SS2} = 0V$ ,  $V_{OF} = 3.3V$ ,  $T_I = 25^{\circ}$ C)

(Over operating	i	H DD1 DD.	2 120,0	L SS1 SS	2 <b>0 v</b> , <b>v</b> <sub>OE</sub>	0.0 v, 1 j 20 0)
Sym	Parameter	Min	Тур	Max	Units	Conditions
V <sub>DD</sub> - V <sub>SS</sub>	Logic supply voltage	4.5	-	13	V	
V <sub>ss</sub>	Logic side supply voltage	-5.5	-	0	V	
$V_{H}$	Output high supply voltage	V <sub>SS</sub> + 2.0	-	V <sub>DD</sub>	V	
$V_L$	Output low supply voltage	V <sub>ss</sub>	-	V <sub>DD</sub> - 2.0	V	
I <sub>DD1Q</sub>	V <sub>DD1</sub> quiescent current	-	0.55	-	mA	
I <sub>DD2Q</sub>	V <sub>DD2</sub> quiescent current	-	-	10	μA	No input transitions
I <sub>HQ</sub>	V <sub>H</sub> quiescent current	-	-	10	μA	
I <sub>DD1</sub>	V <sub>DD1</sub> average current	-	0.88	-	mA	
l <sub>DD2</sub>	V <sub>DD2</sub> average current	-	6.6	-	mA	One channel on at 5.0Mhz, No load
I <sub>H</sub>	V <sub>H</sub> average current	-	23	-	mA	110 1000
V <sub>IH</sub>	Input logic voltage high	V <sub>OE</sub> - 0.3	-	5.0	V	
V <sub>IL</sub>	Input logic voltage low	0	-	0.3	V	For logic inputs INL and INL
I <sub>IH</sub>	Input logic current high	-	-	1.0	μA	For logic inputs IN <sub>A</sub> and IN <sub>B</sub>
I <sub>IL</sub>	Input logic current low	-	-	1.0	μA	

# **Outputs** $(V_H = V_{DD1} = V_{DD2} = 12V, V_L = V_{SS1} = V_{SS2} = 0V, V_{OE} = 3.3V, T_J = 25^{\circ}\text{C})$

Sym	Parameter	Min	Тур	Max	Units	Conditions
V <sub>IH</sub>	OE Input logic voltage high	1.2	-	5.0	V	
V <sub>IL</sub>	OE Input logic voltage low	0	-	0.3	V	For logic input OE
R <sub>IN</sub>	Input logic impedance to GND	12	20	30	ΚΩ	
C <sub>IN</sub>	Logic input capacitance	-	5.0	10	pF	All inputs
$\theta_{JA}$	Thermal resistance to air	-	47	-	°C/W	1oz. 4-layer 3x4" PCB with thermal pad and thermal via array
$\theta_{JC}$	Thermal resistance to case	-	7.0	-	°C/W	
R <sub>SINK</sub>	Output sink resistance	-	-	12.5	Ω	I <sub>SINK</sub> = 50mA
R <sub>SOURCE</sub>	Output source resistance	-	-	12.5	Ω	I <sub>SOURCE</sub> = 50mA
ISINK	Peak output sink current	-	2.0	-	Α	
SOURCE	Peak output source current	_	2.0	-	Α	

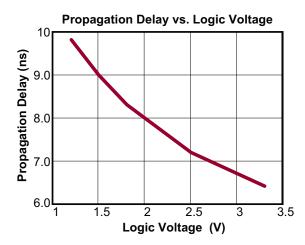
# **AC Electrical Characteristics** $(V_H = V_{DD1} = V_{DD2} = 12V, V_L = V_{SS1} = V_{SS2} = 0V, V_{OE} = 3.3V, T_J = 25^{\circ}C)$

Sym	Parameter	Min	Тур	Max	Units	Conditions
t	Inputs or OE rise & fall time	-	-	10	ns	Logic input edge speed requirement
t <sub>PLH</sub>	Propagation delay when output is from low to high	-	7.0	-	ns	
t <sub>PHL</sub>	Propagation delay when output is from high to low	-	7.0	-	ns	C <sub>LOAD</sub> = 1000pF,
t <sub>POE</sub>	Propagation delay OE to outputs	ı	9.0	-	ns	see timing diagram Input signal rise/fall time of 2ns
t <sub>r</sub>	Output rise time	-	6.0	-	ns	
t <sub>f</sub>	Output fall time	-	6.0	-	ns	
lt <sub>r</sub> - t <sub>f</sub> l	Rise and fall time matching	-	1.0	-	ns	
I t <sub>PLH</sub> -t <sub>PHL</sub> I	Propagation low to high and high to low matching	-	1.0	-	ns	For each channel
$\Delta t_{_{dm}}$	Propagation delay match	-	±2.0	-	ns	Device to device delay match

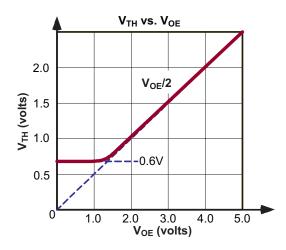
## **Logic Truth Table**

	Logic Inputs	Output				
OE	IN <sub>A</sub>	IN <sub>B</sub>	OUT <sub>A</sub>	OUT <sub>B</sub>		
Н	L	L	V <sub>H</sub>	V <sub>H</sub>		
Н	L	Н	V <sub>H</sub>	V <sub>L</sub>		
Н	Н	L	V <sub>L</sub>	V <sub>H</sub>		
Н	Н	Н	V <sub>L</sub>	V <sub>L</sub>		
L	X	X	V <sub>H</sub>	V <sub>L</sub>		

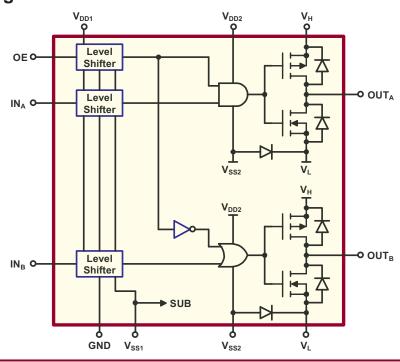
## **Propagation Delay**



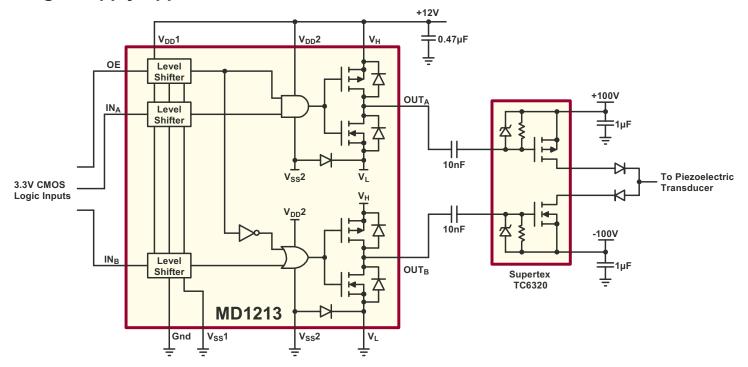
## **Logic Input Threshold**



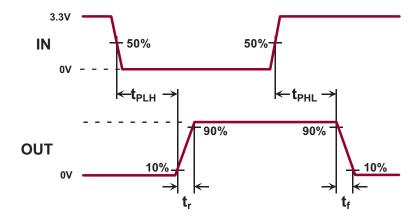
## **Detailed Block Diagram**



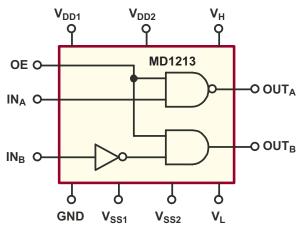
## **Single Supply Application Circuit**



## **Timing Diagram**



## Simplified Block Diagram



#### **Application Information**

For proper operation of the MD1213, low inductance bypass capacitors should be used on the various supply pins. The GND input pin should be connected to the digital ground. The INA, INB, and OE pins should be connected to their logic source with a swing of GND to logic level high, which is 1.2V to 5.0V. Good trace practices should be followed corresponding to the desired operating speed. The internal circuitry of the MD1213 is capable of operating up to 100MHz, with the primary speed limitation being the loading effects of the load capacitance. Because of this speed and the high transient currents that result with capacitive loads, the bypass capacitors should be as close to the chip pins as possible. Unless the load specifically requires bipolar drive, the V<sub>SS1</sub>, V<sub>ss2</sub>, and V<sub>i</sub> pins should have low inductance feed-through connections directly to a ground plane. If these voltages are not zero, then they need bypass capacitors in a manner similar to the positive power supplies. The power connections  $V_{DD1}$  and  $V_{DD2}$  should have a ceramic bypass capacitor to the ground plane with short leads and decoupling components to prevent resonance in the power leads. A common capacitor and voltage source may be used for these two pins, which should always have the same DC voltage applied. For applications sensitive to jitter and noise, separate decoupling networks may be used for  $V_{DD1}$  and  $V_{DD2}$ .

The supplied voltages of  $V_{\rm H}$  and  $V_{\rm L}$  determine the output logic levels. These two pins can draw fast transient currents of up to 2.0A, so they should be provided with an appropriate bypass capacitor located next to the chip pins. A ceramic capacitor of up to 1.0µF may be appropriate, with a series ferrite bead to prevent resonance in the power supply lead coming to the capacitor. Pay particular attention to minimizing trace lengths and using sufficient trace width to reduce inductance. Surface mount components are highly recommended. Since the output impedance of this driver is very low, in some cases it may be desirable to add a small series resistor in series with the output signal to obtain better waveform integrity at the load terminals.

This will of course reduce the output voltage slew rate at the terminals of a capacitive load. Pay particular attention to the parasitic coupling from the driver output to the input signal terminals. This feedback may cause oscillations or spurious waveform shapes on the edges of signal transitions. Since the input operates with signals down to 1.2V, even small coupled voltages may cause problems. Use of a solid ground plane and good power and signal layout practices will prevent this problem. Be careful that the circulating ground return current from a capacitive load cannot react with common inductance to cause noise voltages in the input logic circuitry.

### **Pin Description**

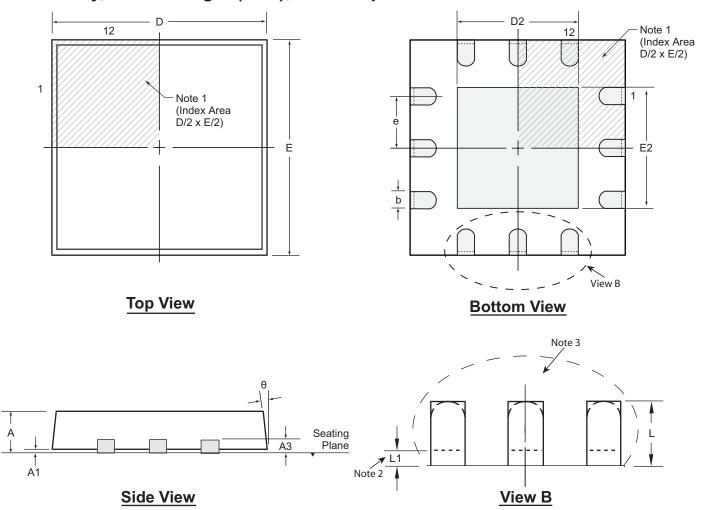
Pin#	Name	Description
-1 111 11	Mairie	•
1	IN <sub>A</sub>	Logic input. Controls $OUT_A$ when $OE$ is high. Input logic high will cause the output to swing to $V_L$ . Input logic low will cause the output to swing to $V_H$ .
2	$V_L$	Supply voltage for N-channel output stage.
3	IN <sub>B</sub>	Logic input. Controls $OUT_B$ when $OE$ is high. Input logic high will cause the output to swing to $V_L$ . Input logic low will cause the output to swing to $V_H$ .
4	GND	Logic input ground reference.
5	V <sub>ss1</sub>	Low side analog circuit and level shifter supply voltage. Should be at the same potential as $V_{\rm SS2}$ .
6	$V_{SS2}$	Low side gate drive supply voltage.
7	OUT <sub>B</sub>	Output driver. Swings from $V_H$ to $V_L$ . Intended to drive the gate of an external N-channel MOSFET via a series capacitor. When OE is low, the output is disabled. $OUT_B$ will swing to $V_L$ turning off the external N-channel MOSFET.
8	V <sub>H</sub>	Supply voltage for P-channel output stage.
9	OUT <sub>A</sub>	Output driver. Swings from $V_H$ to $V_L$ . Intended to drive the gate of an external P-channel MOSFET via a series capacitor. When OE is low, the output is disabled. $OUT_A$ will swing to $V_H$ turning off the external P-channel MOSFET.
10	$V_{_{\mathrm{DD2}}}$	High side gate drive supply voltage.
11	V <sub>DD1</sub>	High side analog circuit and level shifter supply voltage. Should be at the same potential as $V_{\tiny DD2}$ .
12	OE	Output-enable logic input. When OE is high, $(V_{OE} + V_{GND})/2$ sets the threshold transition between logic level high and low for $IN_A$ and $IN_B$ . When OE is low, $OUT_A$ is at $V_H$ and $OUT_B$ is at $V_L$ regardless of $IN_A$ and $IN_B$

**Note:** 1.Thermal Pad and Pin#5 ( $V_{SS1}$ ) must be connected externally.

2. Index Pad and Thermal Pad are connected internally

# 12-Lead QFN Package Outline (K6)

4x4mm body, 1.0mm height (max), 0.80mm pitch



#### Notes:

- 1. Details of Pin 1 identifier are optional, but must be located within the indicated area. The Pin 1 identifier may be either a mold, or an embedded metal or marked feature.
- 2. Depending on the method of manufacturing, a maximum of 0.15mm pullback (L1) may be present.
- 3. The inner tip of the lead may be either rounded or square.

Symb	ol	Α	A1	А3	b	D	D2	E	E2	е	L	L1	θ
	MIN	0.80	0.00		0.20		2.00		2.00		0.30	0.03	0°
Dimension (mm)	NOM	0.90	0.02	0.20 REF	0.30	4.00 BSC	2.15	4.00 BSC	2.15	0.80 BSC	-	-	-
(111111)	MAX	1.00	0.05		0.35	BSC	2.25		2.25	500	0.50	0.15	14°

Drawings not to scale.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <a href="http://www.supertex.com/packaging.html">http://www.supertex.com/packaging.html</a>.)

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Тел: +7 (812) 336 43 04 (многоканальный) Email: org@lifeelectronics.ru